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April 27, 2005

Time: 1:40 P.M.
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TO: Commissioner for Patents
Attn: Theresa Doan
Patent Examining Corps
Facsimile Center
P.O. Box 1450
Alexandria, VA 22313-1450

FAX NUMBER 703-[redacted] 872-9306

FROM: Eric H. Olson

OUR REF: 303.355US4

TELEPHONE: 612-371-2131

*** Please deliver to Examiner Theresa Doan in Art Unit 2814. ***

Total pages of this transmission, including cover letter: 12 pgs.
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In re. Patent Application of: Leonard Forbes et al.
Serial No.: 09/883,795
Filed: June 18, 2001
Title: METHOD OF FORMING A DEVICE WITH A GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE

Examiner: Theresa Doan
Group Art Unit: 2814
Docket No.: 303.355US4

I hereby certify that this paper is being transmitted by facsimile to the U.S. Patent and Trademark Office on the date shown below.

Eric H Olson

Date of Transmission 5/4/05

PATENT

S/N Unknown

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Leonard Forbes et al.	Examiner: Unknown
Serial No.:	Unknown	Group Art Unit: Unknown
Filed:	Herewith	Docket: 303.355US4
Title:	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE	

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
Washington, D.C. 20231

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for review in connection with the above-identified patent application. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner be returned to the Applicants.

In accordance with 37 C.F.R. §1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicants' prior U.S. application, Serial No. 09/141,392, filed on August 27, 1998, which is relied upon for an earlier filing date under 35 U.S.C. §120.

Applicants respectfully request consideration of these references during prosecution of the above-identified matter. The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

LEONARD FORBES ET AL.

By their Representatives,

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Date 18 JUNE 2001 By _____

Robert E. Mates
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Form 1449*	Atty. Docket No.: 303.355US4	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown

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